ABSTRACT

SUBSTRATE PROCESSING APPARATUS, METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE AND SUBSTRATE PROCESSING PROGRAM

Described herein is a technique capable of adjusting an inner pressure of a process chamber into a high vacuum state in a short time. According to one aspect of the technique, there is provided a substrate processing apparatus including: a process chamber; a pressure sensor; a first pipe; a first exhaust line comprising a first opening degree adjustment valve; a second pipe connected to the first exhaust line; a second exhaust line comprising a second opening degree adjustment valve; and a control unit. The control unit adjusts the opening degree of the second opening degree adjustment valve to bring the pressure in the process chamber to the processing pressure when the processing pressure is higher than the predetermined vacuum level, and the control unit adjusts the opening degree of the first opening degree adjustment valve to bring the pressure in the process chamber to the processing pressure when the processing pressure is lower than the predetermined vacuum level.

Figure 1